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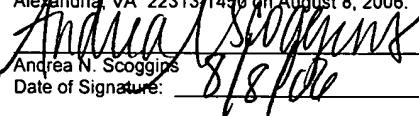
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Andrea N. Scoggins
Date of Signature: 8/8/06

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Re: U.S. National Phase Application No. 10/550,040 for
METHODS AND SYSTEMS FOR SINGLE OR MULTI-PERIOD EDGE
DEFINITION LITHOGRAPHY based on PCT/US04/08724
NCSU Ref. No. 03-119; Our Ref. No. 297/171 PCT/US

Sir:

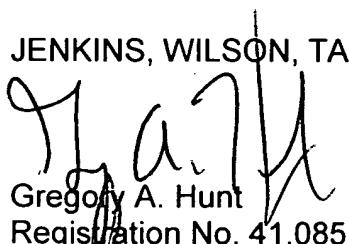
Please find enclosed in connection with the subject U.S. patent application the following documents:

1. Supplemental Information Disclosure Statement (2 pages);
2. Form PTO-1449 (4 pages) in duplicate;
3. Copies of cited references (21 references); and
4. A return-receipt postcard to be returned to us with the U.S. Patent and Trademark Office filing stamp thereon.

The Commissioner is hereby authorized to charge any fees associated with the filing of this correspondence to Deposit Account No. 50-0426.

Respectfully submitted,

JENKINS, WILSON, TAYLOR & HUNT, P.A.


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Registration No. 41,085

GAH/ans
Enclosures

Customer No: 25297



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8/8/06

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Johnson et al.

Group Art Unit: Unassigned

Serial No.: 10/550,040

Examiner: Unassigned

Filed: September 21, 2005

Docket No.: 297/171 PCT/US

Confirmation No.: 8058

For: METHODS AND SYSTEMS FOR SINGLE OR MULTI-PERIOD EDGE DEFINITION LITHOGRAPHY

* * * * *

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with 37 C.F.R. 1.56, 1.97, and 1.98, applicants' undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO-1449. Pursuant to 37 C.F.R. § 1.98(a)(2)(i), copies of the U.S. patents and U.S. patent application publication references cited on the attached Form PTO-1449 are not attached. However, copies can be provided if necessary. This is not to be construed as a representation that a search has been made or that a reference is relevant merely because cited.

Serial No.: 10/550,040

Early passage of the subject application to issue is earnestly solicited.

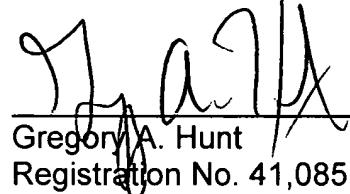
Although it is believed that no fee is due, the Commissioner is hereby authorized to charge any fees associated with the filing of this Information Disclosure Statement to Deposit Account No. 50-0426.

Respectfully submitted,

JENKINS, WILSON, TAYLOR & HUNT, P.A.

Date: 8-8-06

By:



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FORM PTO-146A U.S. Department of Commerce
Patent and Trademark Office

List of Documents Cited by Applicant

Application No.:	10/550,040
Filing Date:	September 21, 2005
First Named Inventor:	Johnson et al.
Group:	Unassigned
Examiner:	Unassigned
Attorney Docket No.:	297/171 PCT/US

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EXAMINER _____

DATE CONSIDERED _____

*Examiner Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.